

TENTATIVE

#### Features and Applications

- High density mounting is possible because of the complex type which holds two chips of a low on-resistance, Very-high speed switching and 2.5-volt-drive, P channel MOSFET in one package.
- The two chips have near characteristics

#### Absolute Maximum Ratings / Ta=25°C

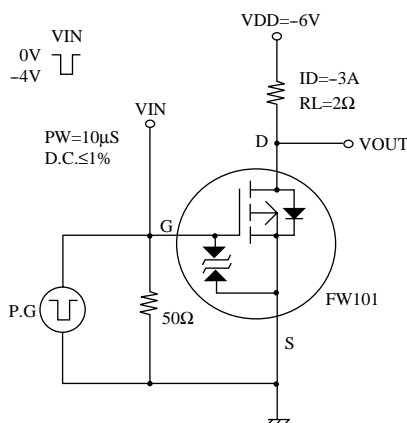
			unit
Drain to Source Voltage	VDSS	-12	V
Gate to Source Voltage	VGSS	±10	V
Drain Current (D.C)	ID	-3	A
Drain Current (Pulse)	IDP	PW≤10μS, dutycycle≤1%	-12 A
Allowable power Dissipation	PD	Mounted on ceramic board (1000mm²×0.8mm)	1.7 W
All Dissipation	PT	Mounted on ceramic board (1000mm²×0.8mm)	2.0 W
Channel Temperature	Tch	150	°C
Storage Temperature	Tstg	-55 to +150	°C

#### Electrical Characteristics / Ta=25°C

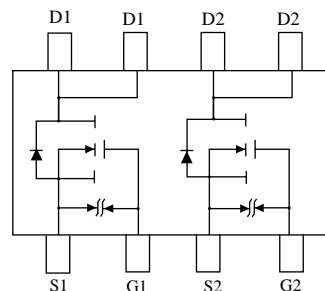
			min	typ	max	unit
Drain to Source Breakdown Voltage	V(BR)DSS	ID=-1mA, VGS=0	-12			V
Zero Gate Voltage Drain Current	IDSS	VDS=-10V, VGS=0			-100	μA
Gate to Source Leakage Current	IGSS	VGS=±8V, VDS=0			±10	μA
Cutoff Voltage	VGS(OFF)	VDS=-6V, ID=-1mA	-0.4		-1.4	V
Forward Transfer Admittance	yfs	VDS=-6V, ID=-3A	5	8		S
Static Drain to Source on State Resistance	RDS(On)1	ID=-3A, VGS=-4V		85	115	mΩ
	RDS(On)2	ID=-1A, VGS=-2.5V		115	165	mΩ
Input Capacitance	Ciss	VDS=-6V, f=1MHz		650		pF
Output Capacitance	Coss	VDS=-6V, f=1MHz		450		pF
Reverse Transfer Capacitance	Crss	VDS=-6V, f=1MHz		150		pF
Turn-ON Delay Time	td(On)	See Specified Test Circuit .		20		ns
Rise Time	tr			260		ns
Turn-off Delay Time	td(Off)			250		ns
Fall Time	tf			280		ns
Diode Forward Voltage	VSD	IS=-3A, VGS=0	-1.0	-1.2		V

Marking : W101

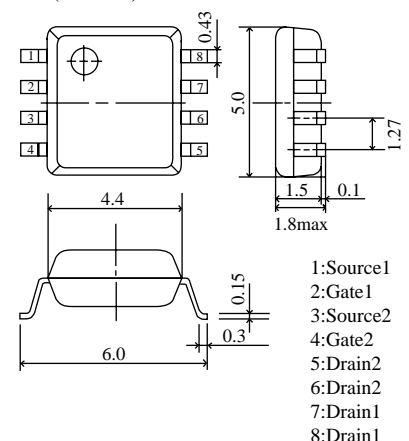
#### Switching Time Test Circuit



#### Electrical Connection (Top View)



#### Case Outline SOP8(unit:mm)



Specifications and information herein are subject to change without notice.

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